



# Structure and microwave dielectric properties of $\text{Ba}_{1-x}\text{Sr}_x\text{Mg}_2\text{V}_2\text{O}_8$ ceramics



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## ABSTRACT

The  $\text{Ba}_{1-x}\text{Sr}_x\text{Mg}_2\text{V}_2\text{O}_8$  ( $0 \leq x \leq 0.4$ ) microwave dielectric ceramics were fabricated by a standard solid-state reaction method. The formation of a continuous solid solution within the whole composition range was identified. The ceramic samples could be well densified in the temperature range of 885–975 °C in air for 4 h. The permittivity  $\epsilon_r$  was found to increase with increasing ionic polarizabilities. The  $Q \times f$  values were believed to be closely related with packing fraction and grain refinement. The  $\text{Sr}^{2+}$  substitution contributed to a monotonous increase of the A-site bond valence, such that the  $\tau_f$  value experienced a considerable variation from negative to positive values. The optimum microwave dielectric properties of an  $\epsilon_r$  of 13.3, a high  $Q \times f$  of 86,640 GHz (9.6 Hz) and a near-zero  $\tau_f$  of  $-6$  ppm/°C could be yielded in the  $x=0.15$  sample when sintered at 915 °C for 4 h.

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## 1. Introduction

A rapid development in wireless communication systems such as satellite positioning, mobile phones and patch antennas has brought demands for high-performance microwave devices over the past decades [1]. Moreover, the low-temperature cofired ceramic (LTCC) technology for the miniaturization and integration of electronic devices has generally required the corresponding dielectric materials to have a lower sintering temperature than the melting point of the Ag electrode, in addition to an appropriate permittivity ( $\epsilon_r$ ), a high quality factor ( $Q \times f$ ) value, and a near-zero temperature coefficient of resonant frequency ( $\tau_f$ ) [2–3]. Most of microwave dielectric materials need to be densified at higher sintering temperatures [4–7]. This situation can be improved through the addition of low melting glass, chemical processing or use of fine raw materials [8–10]. However, the complicated fabrication processing and deteriorated microwave dielectric properties have become challenges for the application of these LTCC materials. A glass-free LTCC material with desirable microwave dielectric properties is therefore of much interest. A lot of efforts have been recently focused on some  $\text{Li}_2\text{O}$ -,  $\text{TeO}_2$ -,  $\text{Bi}_2\text{O}_3$ -,  $\text{MoO}_3$ - and  $\text{V}_2\text{O}_5$ -based compounds with intrinsically low sintering temperatures and desirable performances [11–20]. For example, some vanadates with a garnet structure were reported to show great potentials in LTCC applications [21–23].

The  $\text{BaMg}_2\text{V}_2\text{O}_8$  ceramic with a body-centered tetragonal

structure demonstrated excellent microwave dielectric properties of  $\epsilon_r=12$ ,  $Q \times f=156,140$  GHz (9.9 GHz) and  $\tau_f=-36$  ppm/°C as sintered at a relatively low temperature of 900 °C [24]. The low-firing characteristics and ultra-low loss probably make it be a promising candidate for advanced substrate materials used in microwave integrated circuits. However, the negative  $\tau_f$  value might strongly restrict its application in LTCC-based devices. A  $\text{BaMg}_2\text{V}_2\text{O}_8\text{-TiO}_2$  composite was prepared in our previous work using two materials with opposite signs of  $\tau_f$ . This approach can well explain the variation of  $\tau_f$  values from the viewpoint of the two-phase coexistence. In addition, the A-site ionic substitution has been widely attempted owing to its role in tailoring the undesirable  $\tau_f$  value of the matrix by forming a solid solution. It was previously revealed that the substitution of smaller Ni ions (0.69 Å, CN=6) for Zn ions (0.74 Å, CN=6) contributed to the decrease of the A-site bond valence and consequently the decrease of  $\tau_f$  values in the monoclinic structured  $(\text{Zn}_{1-x}\text{Ni}_x)_3\text{Nb}_2\text{O}_8$  system [25]. Moreover, the increase of the oxygen bond valence in tetragonal scheelite compounds was reported to result in the increase of the average bond strength of A-site and B-site ions, which in turn enhanced the restoring force for the tilting of  $\text{A}_2\text{BO}$  tetrahedra, such that the  $\tau_f$  value decreased [26]. For perovskite solid solutions, the  $\tau_f$  values are usually affected by either the variation of polarizability per unit cell or a phase transition associated with octahedral rotations [27–29]. The substitution of smaller A-site ions for  $\text{Ba}^{2+}$  in  $\text{Ba}_3\text{MM}'_2\text{O}_9$  ( $\text{M}=\text{Mg}, \text{Ni}, \text{Zn}$ ;  $\text{M}'=\text{Nb}, \text{Ta}$ ) perovskites was believed to contribute to the change of octahedral tilting, therefore producing a corresponding adjustment of  $\tau_f$  [30].

In current work,  $\text{Sr}^{2+}$  was anticipated to occupy the A-site in the  $\text{BaMg}_2\text{V}_2\text{O}_8$  lattice within the entire composition range. The

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